Silicon Carbide (SiC), 30 mohm, 2200 V, TO-247C Plus-4L QX4L030N220C

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
2200 V	30mΩ	100A

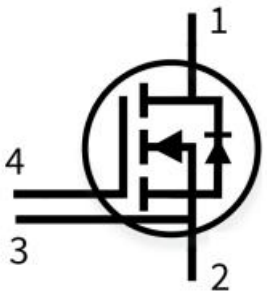
Features

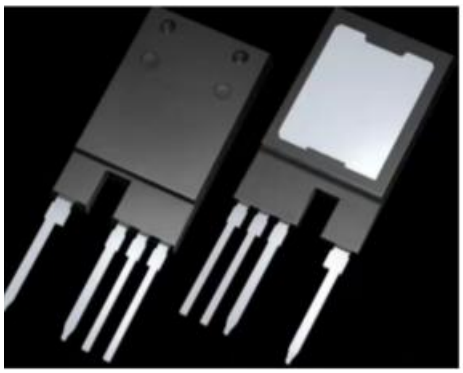
- Typ. $R_{DS(on)}$ = 30mΩ @ V_{GS} = 18V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 136nC)
- High Speed Switching with Low Capacitance(C_{oss}=168pF)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb−Free 2LI (on second level interconnection)

Typical Applications

- Solar Inverters
- Electric Vehicle Charging Stations
- UPS (Uninterruptible Power Supplies)
- Energy Storage Systems
- SMPS (Switch Mode Power Supplies)

N−CHANNEL MOSFET





TO−247C Plus−4L

MAXIMUM RATINGS (T_j = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	2200	V
Gate−to−Source Voltage			V_{GS}	−10/+22	V
Recommended Operation Values of Gate−to−Source Voltage		T_C < 175°C	V_{GSOP}	−4/+18	V
Continuous Drain Current (Notes 1, 3)	Steady State	T_C = 25°C	I_D	100	A
Power Dissipation (Note 1)	Steady State	T_C = 25°C	P_D	576	W
Continuous Drain Current (Notes 1, 3)	Steady State	T_C = 100°C	I_D	63	A
Power Dissipation (Note 1)	Steady State	T_C = 100°C	P_D	288	W
Pulsed Drain Current	T_C = 25°C		I_{DM}	189	A
Operating Junction and Storage Temperature Range			T_j, T_{stg}	−55 to +175	°C
Source Current (Body Diode) T_C=25°C, V_{GS} = −3V			I_S	100	A
Single Pulse Drain−to−Source Avalanche Energy (Note 4)			E_{AS}	750	mJ
Maximum Lead Temperature for Soldering (1/25 from case for 10 s)			T_L	270	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. The maximum current rating is based on typical $R_{DS(on)}$ performance.
4. E_{AS} of 750 mJ is based on starting T_j = 25°C; L = 1mH, I_{AS} = 100 A, V_{DD} = 100 V, V_{GS} = 18 V.

ORDERING INFORMATION

Device	Package	Shipping
QX4L030N220C	TO−247C Plus−4L	30 Units / Tube

TYPICAL CHARACTERISTICS

Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction−to−Case −Steady State (Note 1)	$R_{\theta JC}$	0.26	°C/W
Junction−to−Ambient −Steady State (Note 1)	$R_{\theta JA}$	62	°C/W

Table 2. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF−STATE CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250uA		2200	−	−	V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_j$	I_D = 250uA, referenced to 25°C		−	0.3	−	V/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0V, V_{DS} = 2200V, T_j = 25°C		−	−	400	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = +4/−18V, V_{DS} = 0V		−	−	1	μA
ON−STATE CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 37mA		1.8	2.5	4.1	V
Recommended Gate Voltage	V_{GOP}			−4	−	+18	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 18V, I_D = 40A	T_j = 25°C	−	28.3	31.5	mΩ
			T_j =125°C	−	48.1	−	mΩ
			T_j =175°C	−	63.2	−	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 10V, I_D = 40A		−	20	−	S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{iss}	V_{GS} = 0V, f = 100KHz, V_{DS} = 1200V		−	5400	−	pF
Output Capacitance	C_{oss}			−	168	−	pF
Reverse Transfer Capacitance	C_{rss}			−	8.6	−	pF
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4/18V, V_{DS} = 1200V		−	136	−	nC
Threshold Gate Charge	$Q_{G(TH)}$			−	15.8	−	nC
Gate−to−Drain Charge	Q_{GD}			−	59.5	−	nC
Gate−Resistance	R_G	V_{GS} = 0V, f = 1MHz		−	1.32	−	Ω
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$T_{d(on)}$	V_{GS} = −4V/18V, V_{DS} = 1200V, I_D = 40A, R_G = 2Ω, Inductive load	T_j = 25°C	−	33.9	−	ns
			T_j = 125°C	−	36.1	−	ns
			T_j = 175°C	−	18.8	−	ns
Rise Time	t_r		T_j = 25°C	−	23.6	−	ns
			T_j =125°C	−	20.4	−	ns
			T_j = 175°C	−	16.6	−	ns
Turn−Off Delay Time	$T_{d(off)}$		T_j = 25°C	−	45.1	−	ns
			T_j =125°C	−	40.3	−	ns
			T_j = 175°C	−	34.5	−	ns
Fall Time	t_f		T_j = 25°C	−	16.1	−	ns
			T_j =125°C	−	16.1	−	ns
			T_j = 175°C	−	13.7	−	ns

Turn−On Switching Loss	E_{on}	V_{GS} = −4V/18V, V_{DS} = 1200V, I_D = 40A, R_G = 2Ω, Inductive load	T_j = 25°C	−	679.2	−	μJ
			T_j =125°C	−	569.8	−	μJ
			T_j = 175°C	−	460.2	−	μJ
Turn−Off Switching Loss	E_{off}		T_j = 25°C	−	127.3	−	μJ
			T_j =125°C	−	121.9	−	μJ
			T_j = 175°C	−	99.8	−	μJ
Total Switching Loss	E_{tot}		T_j = 25°C	−	806.5	−	μJ
			T_j =125°C	−	691.7	−	μJ
			T_j = 175°C	−	560	−	μJ

SOURCE−DRAIN DIODE CHARACTERISTICS

Continuous Source−Drain Diode Forward Current	I_{SD}	V_{GS} = −4V, T_C = 25°C		−	−	100	A
Pulsed Source−Drain Diode Forward Current	I_{SDM}			−	−	189	A
Forward Diode Voltage	V_{SD}	V_{GS} = −4V, I_{SD} = 40A	T_j = 25°C	−	3.91	4.16	V
			T_j =125°C	−	3.57	−	V
			T_j =175°C	−	3.44	−	V

Table 2. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified) (continued)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SOURCE−DRAIN DIODE CHARACTERISTICS							
Reverse Recovery Charge	Q_{rr}	V_{GS} = −4V, I_{SD} = 40A, -dis/dt =1500 A/μs, V_{DS} = 1200V	T_j = 25°C	−	941.5	−	nC
			T_j =125°C	−	2358.8	−	nC
			T_j =175°C	−	2914.7	−	nC
Reverse Recovery Energy	E_{rec}		T_j = 25°C	−	340.5	−	μJ
			T_j =125°C	−	968.3	−	μJ
			T_j =175°C	−	1290.1	−	μJ
Peak Reverse Recovery Current	I_{rrm}		T_j = 25°C	−	102.1	−	A
			T_j =125°C	−	150.3	−	A
			T_j =175°C	−	170.2	−	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. E_{on}/E_{off} result is with body diode.
6. Defined by design, not subject to production test.

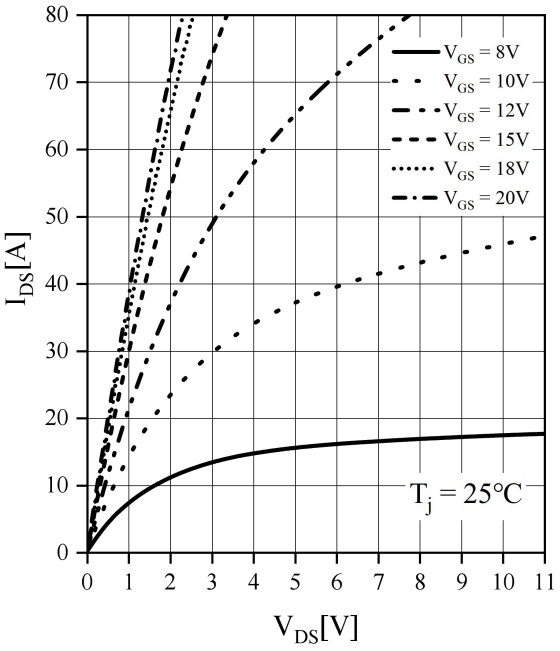


Figure 1. On−Region Characteristics

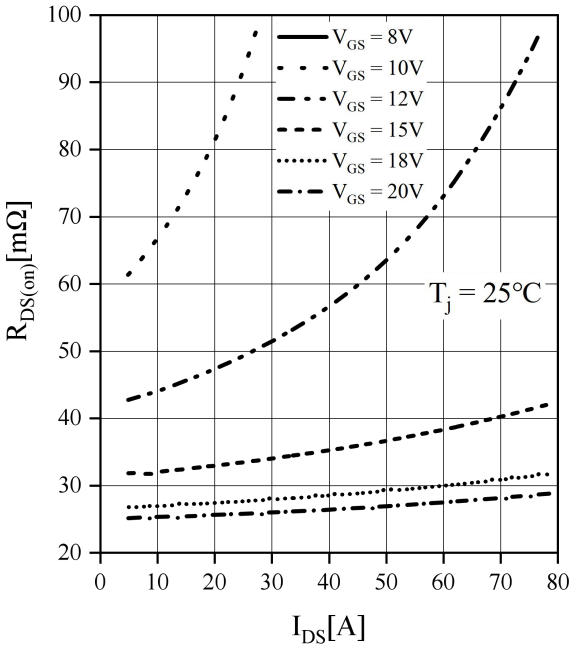


Figure 2. On−Resistance vs. Drain Current and Gate Voltage

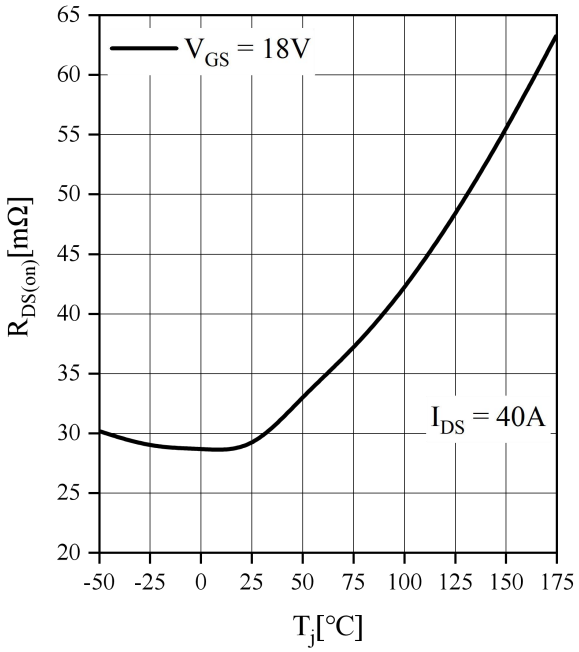


Figure 3. On−Resistance Variation with Temperature

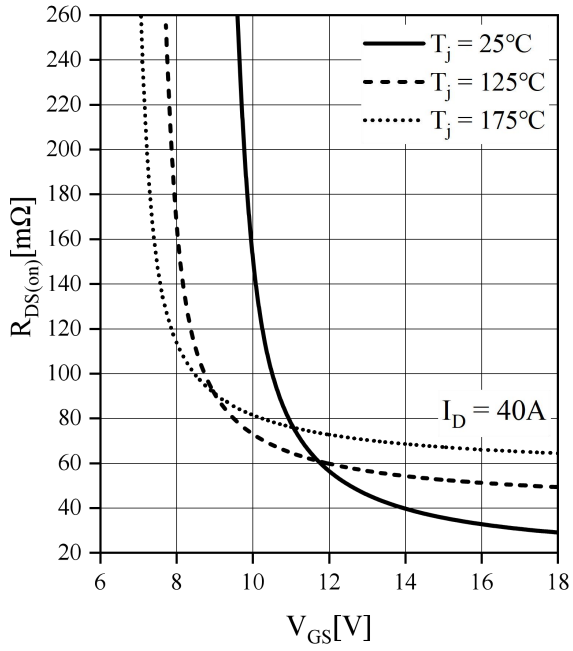


Figure 4. On−Resistance vs. Gate−to−Source Voltage

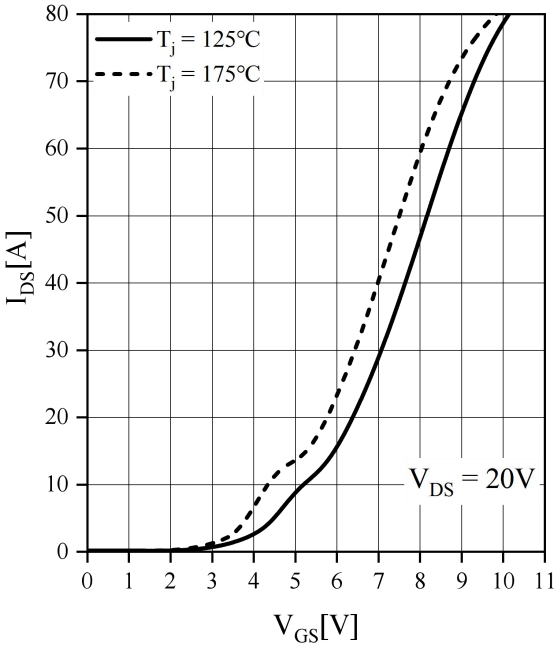


Figure 5. Transfer Characteristics

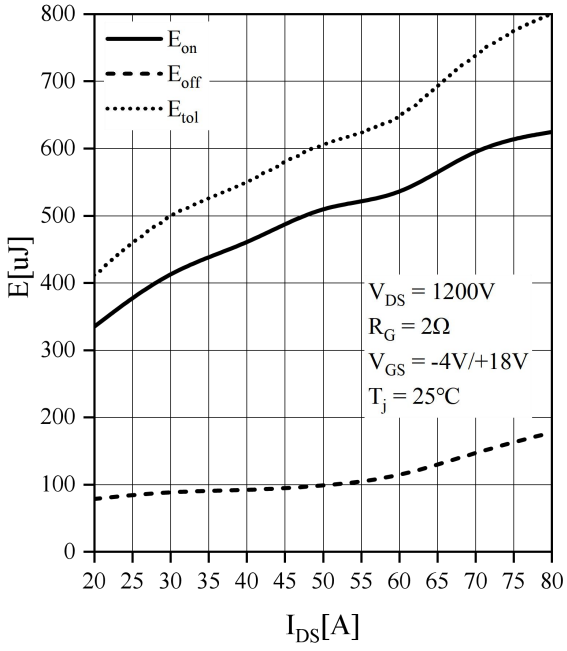


Figure 6. Switching Loss vs. Drain Current

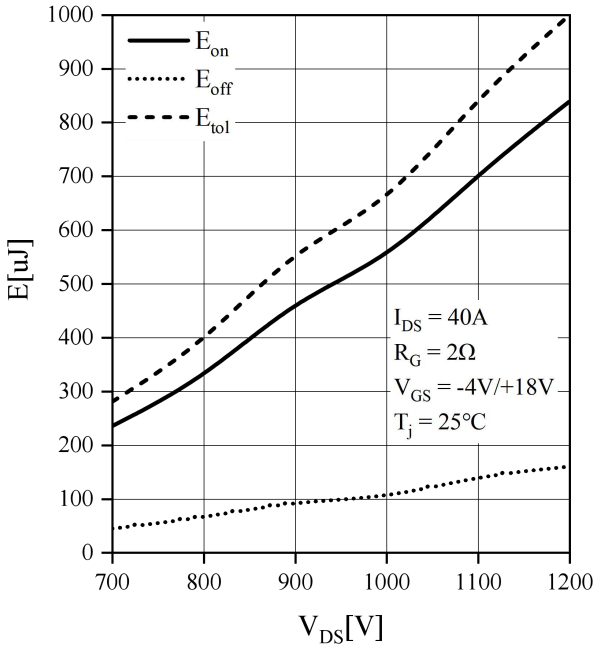


Figure 7. Switching Loss vs. Drain−to−Source Voltage

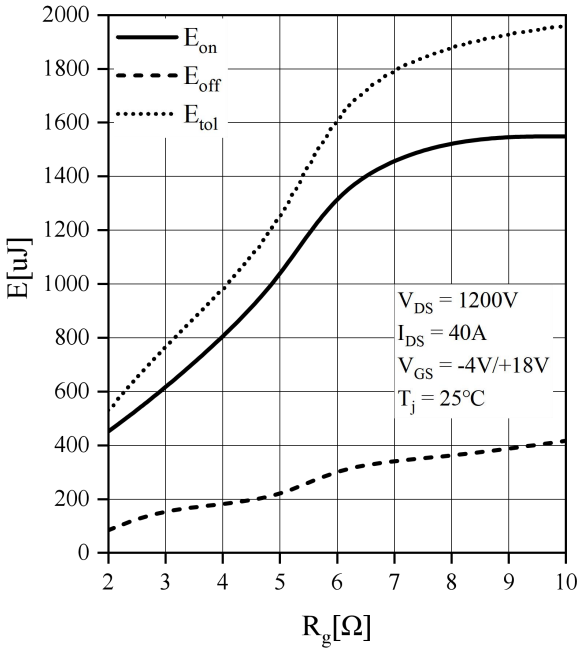


Figure 8. Switching Loss vs. Gate Resistance

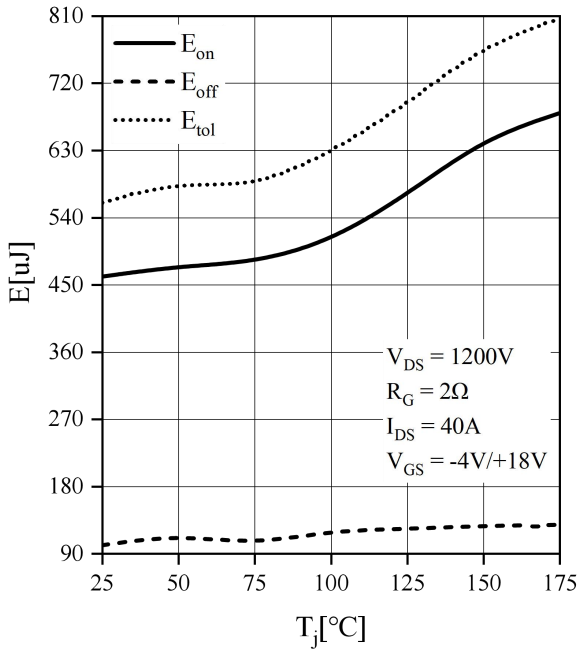


Figure 9. Switching Loss vs. Temperature

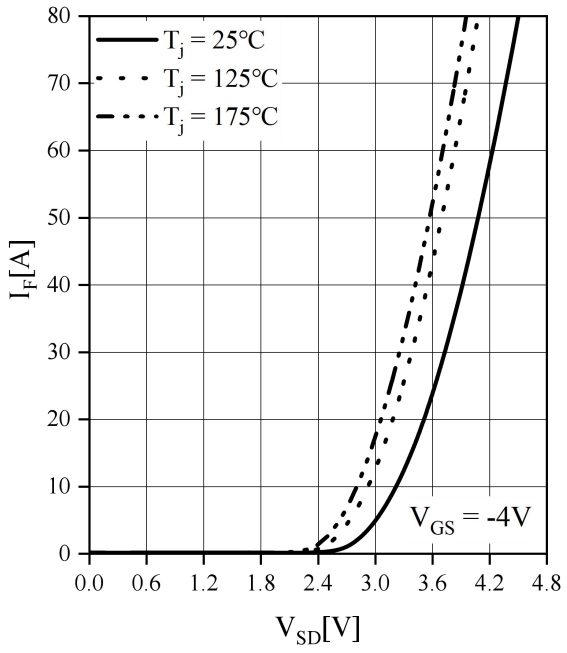


Figure 10. Reverse Drain Current vs. Body Diode Forward Voltage

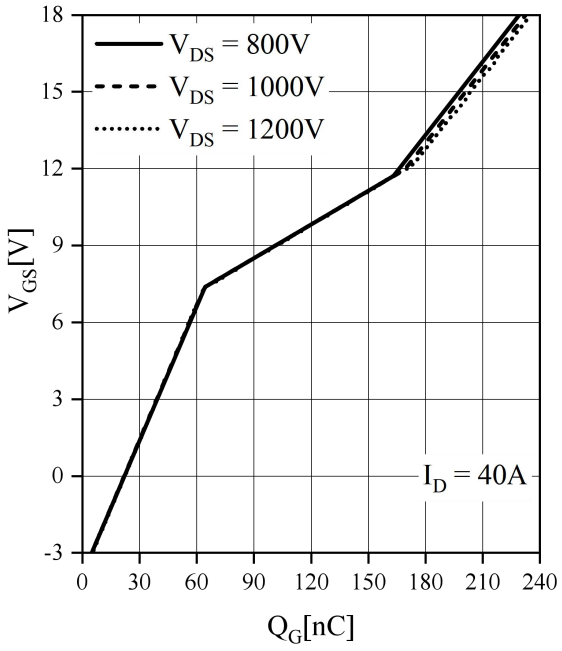


Figure 11. Gate−to−Source Voltage vs. Total Charge

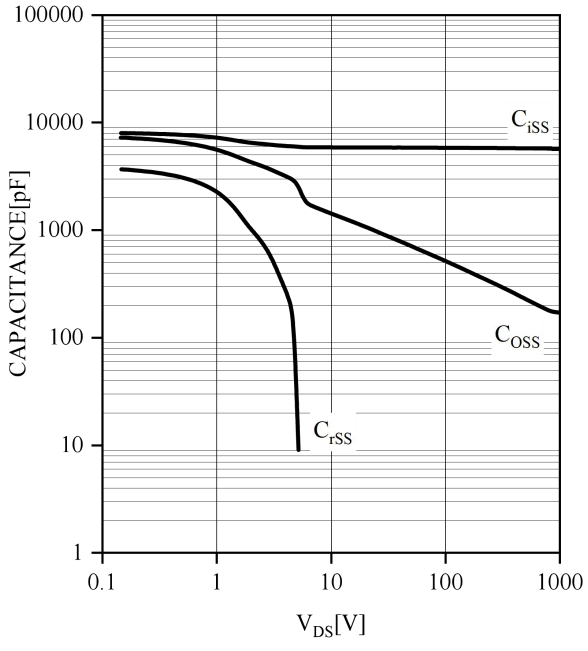


Figure 12. Capacitance vs. Drain−to−Source Voltage

TYPICAL CHARACTERISTICS

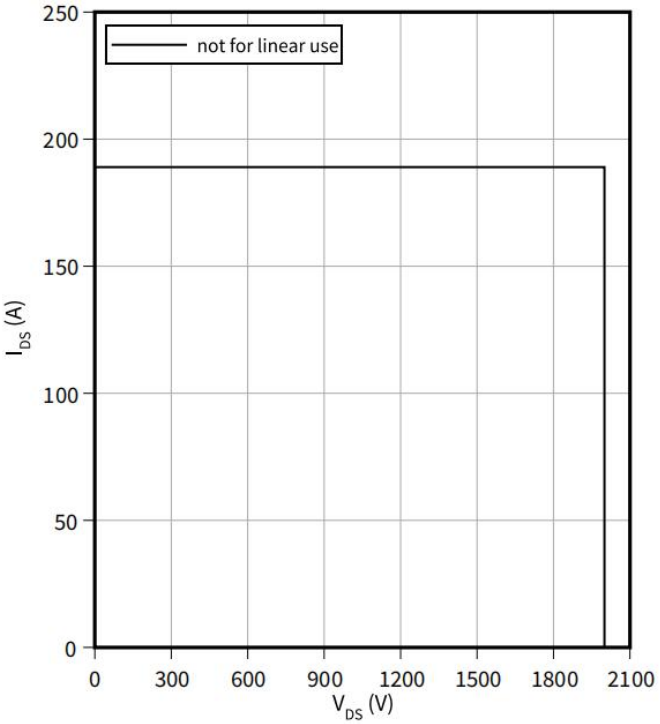


Figure 13. Reverse bias safe operating area (RBSOA)

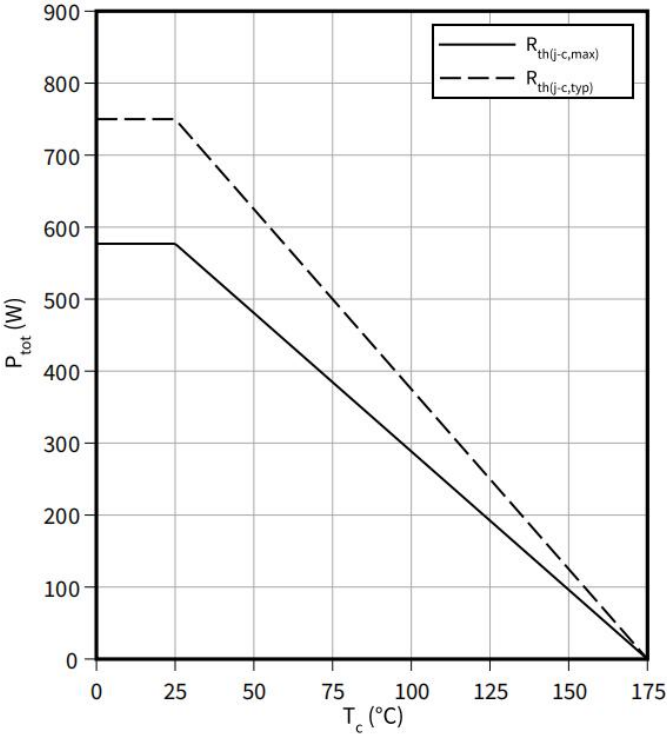


Figure 14. Power dissipation vs. Case temperature

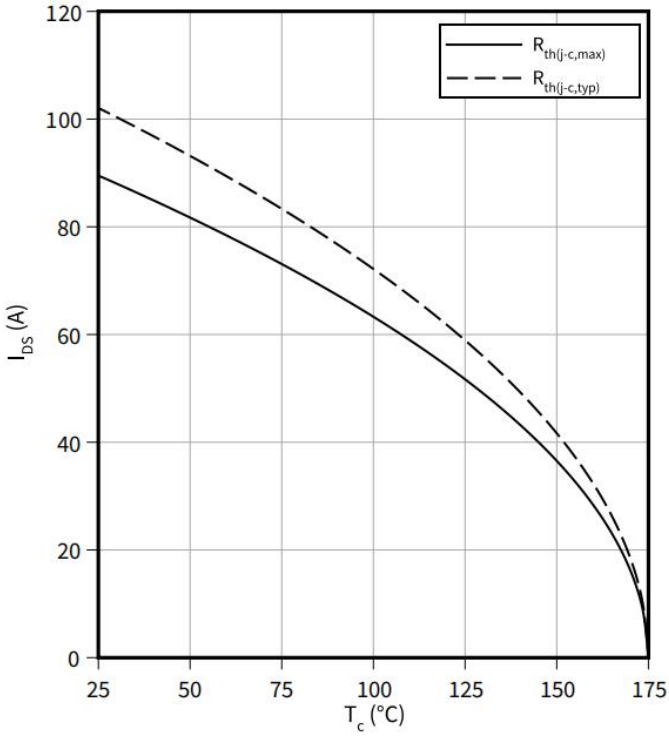


Figure 15. Maximum DC drain to source current vs. Case temperature

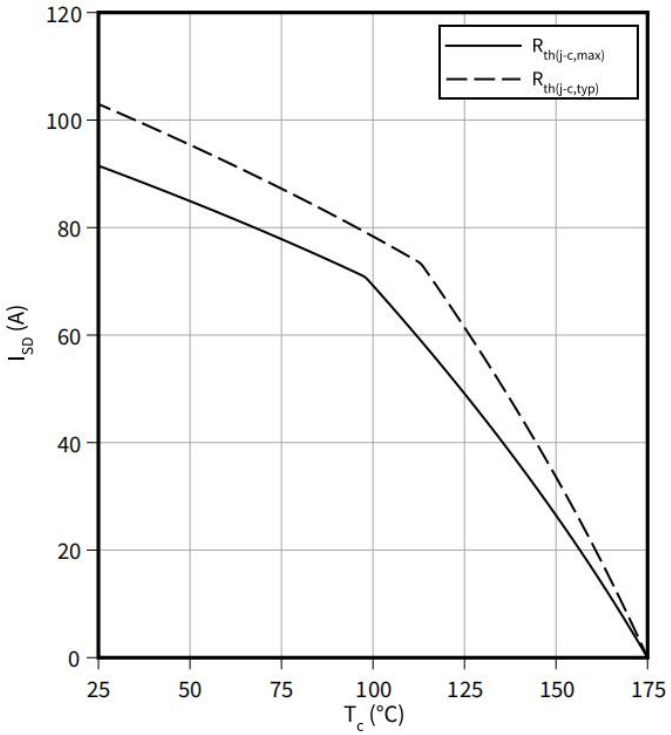
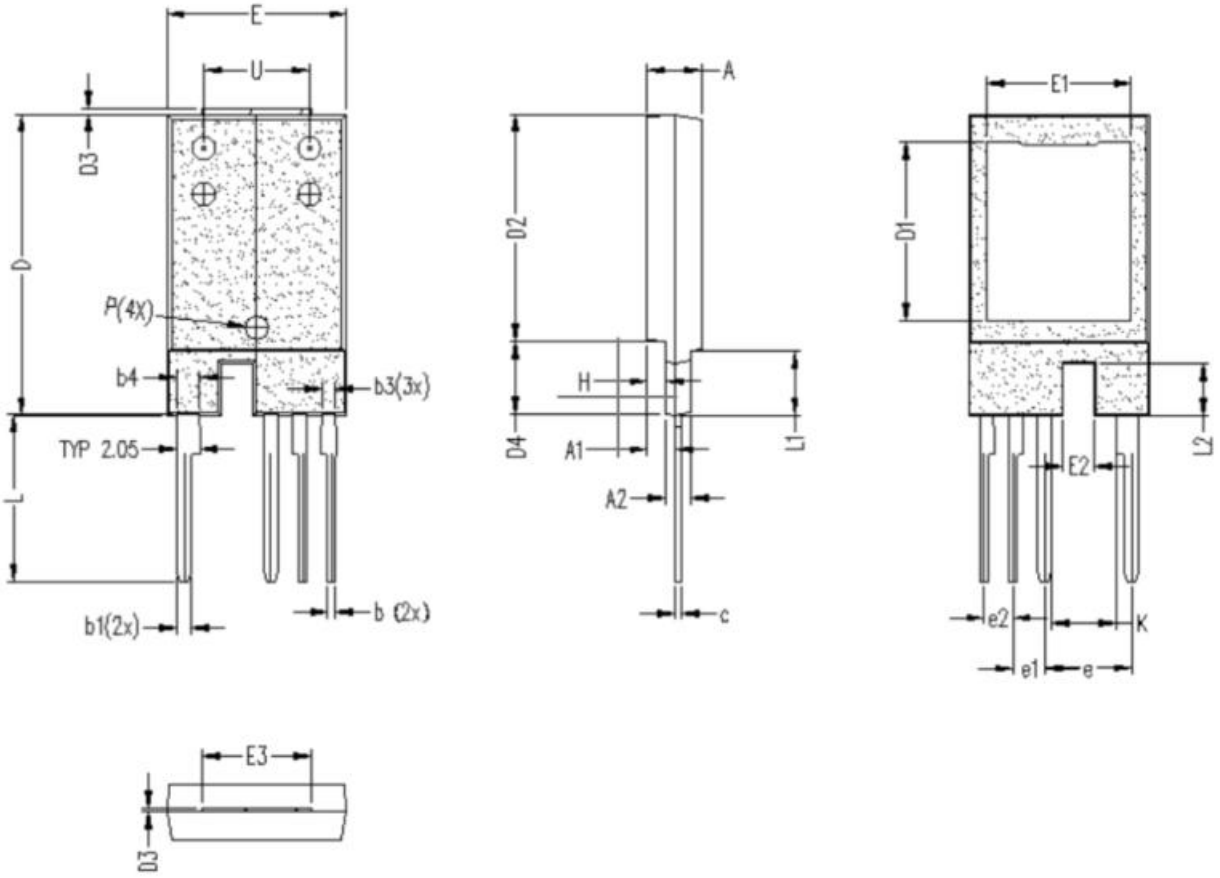


Figure 16.Maximum source to drain current vs. Case temperature

TO-247C Plus-4L PACKAGE OUTLINE DIMENSIONS



DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.65	4.95	**E1**	12.00	12.80
A1	2.16	2.66	**E2**	2.60	3.00
A2	2.00	2.40	**E3**	9.00	10.00
b	0.60	0.80	**e**	7.62	
b1	1.10	1.30	**e1**	2.79	
b2	---	0.15	**e2**	2.54	
b3	1.10	1.30	**H**	1.51	1.71
b4	1.70	2.10	**K**	5.50	---
c	0.50	0.70	**L**	14.30	14.90
D	26.00	26.70	**L1**	5.40	5.70
D1	15.50	16.30	**L2**	4.40	4.70
D2	19.40	20.20	**ØP**	1.75	2.25
D3	---	0.50	**U**	9.00	9.50
D4	6.35	6.65			
E	15.60	16.00			